

## TLVx369 具有零交叉失真的成本优化型 800nA、1.8V、轨到轨 I/O 运算放大器

### 1 特性

- 成本优化型精密放大器，具有毫微功耗：800nA/通道（典型值）
- 低偏移电压：400 $\mu$ V（典型值）
- 轨到轨输入和输出
- 零交叉失真
- 低偏移漂移：0.5 $\mu$ V/ $^{\circ}$ C（典型值）
- 增益带宽积：850MHz
- 电源电压：1.8V 至 5.5V
- 微型封装：SC70-5、VSSOP-8

### 2 应用

- 血糖仪
- 测试设备
- 低功耗传感器信号调节
- 便携式设备

### 3 说明

TLV369 系列单通道和双通道运算放大器是成本优化型 1.8V 毫微功耗放大器的典型代表。

该系列放大器由 1.8V 至 5.5V 的单电源供电运行，并且配有零交叉失真电路，可在整个共模输入范围内保持较高线性度且无交叉失真，从而实现真正的轨到轨输入。该系列还兼容符合行业标准的 3.0V、3.3V 和 5.0V 标称电压。

TLV369（单通道版本）采用 5 引脚 SC70 封装。

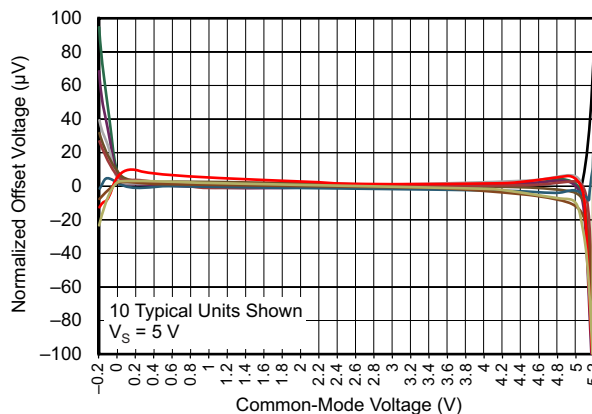
TLV2369（双通道版本）采用 8 引脚超薄小外形尺寸（VSSOP）和小外形尺寸集成电路（SOIC）封装。

器件信息<sup>(1)</sup>

器件型号	封装	封装尺寸（标称值）
TLV369	SC70 (5)	2.00mm x 1.25mm
TLV2369	超薄小外形尺寸封装 (VSSOP) (8)	3.00mm x 3.00mm
	SOIC (8)	4.90mm x 3.91mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

### TLV369 系列消除了整个电源电压范围内的交叉失真



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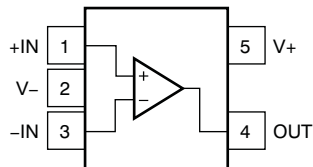
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## 4 修订历史记录

日期	修订版本	注释
2016 年 5 月	*	首次发布。

## 5 Pin Configuration and Functions

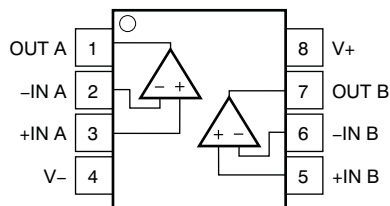
TLV369: DCK Package  
5-Pin SC70  
Top View



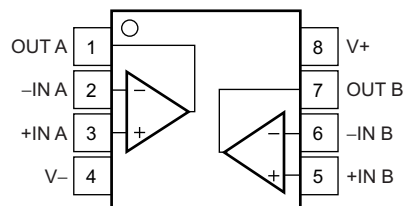
Pin Functions: TLV369

NAME	PIN		I/O	DESCRIPTION
	TLV369	DCK (SC70)		
-IN		3	I	Negative (inverting) input
+IN		1	I	Positive (noninverting) input
OUT		4	O	Output
V-		2	—	Negative (lowest) power supply or ground (for single-supply operation)
V+		5	—	Positive (highest) power supply

TLV2369: D Package  
8-Pin SOIC  
Top View



TLV2369: DGK Package  
8-Pin VSSOP  
Top View



Pin Functions: TLV2369

NAME	PIN		I/O	DESCRIPTION
	TLV2369			
	D (SOIC)	DGK (VSSOP)		
-IN A	2	2	I	Inverting input, channel A
-IN B	6	6	I	Inverting input, channel B
+IN A	3	3	I	Noninverting input, channel A
+IN B	5	5	I	Noninverting input, channel B
OUT A	1	1	O	Output, channel A
OUT B	7	7	O	Output, channel B
V-	4	4	—	Negative (lowest) power supply
V+	8	8	—	Positive (highest) power supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup>

		MIN	MAX	UNIT
Voltage	Supply, $V_S = (V+) - (V-)$	0	+7	V
	Signal input pin <sup>(2)</sup>	$(V-) - 0.5$	$(V+) + 0.5$	V
Current	Signal input pin <sup>(2)</sup>	-10	10	mA
	Output short-circuit <sup>(3)</sup>	Continuous		mA
Temperature	Operating, $T_A$	-40	125	°C
	Junction, $T_J$		150	°C
	Storage, $T_{stg}$	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that can swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to  $V_S / 2$ , one amplifier per package.

### 6.2 ESD Ratings

over operating free-air temperature range (unless otherwise noted).

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	±4000	V
		Charged device model (CDM), per JEDEC specification JESD22-C101 <sup>(2)</sup>	±1500	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
$V_S$	Supply voltage	1.8		5.5	V
	Specified temperature	-40		85	°C

#### 6.4 Thermal Information: TLV369

THERMAL METRIC <sup>(1)</sup>		TLV369		UNIT
		DCK (SC70)		
		5 PINS		
$R_{\theta JA}$	Junction-to-ambient thermal resistance	293.3		°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	95.2		°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	83.4		°C/W
$\psi_{JT}$	Junction-to-top characterization parameter	2.9		°C/W
$\psi_{JB}$	Junction-to-board characterization parameter	82.4		°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a		°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

#### 6.5 Thermal Information: TLV2369

THERMAL METRIC <sup>(1)</sup>		TLV2369		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	121.5	168.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	66.3	58.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	62.5	88.9	°C/W
$\psi_{JT}$	Junction-to-top characterization parameter	22.8	9.3	°C/W
$\psi_{JB}$	Junction-to-board characterization parameter	61.9	87.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	n/a	n/a	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report, [SPRA953](#).

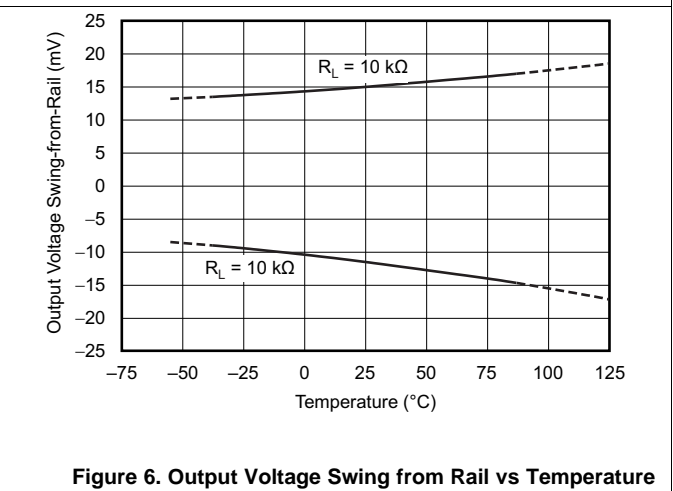
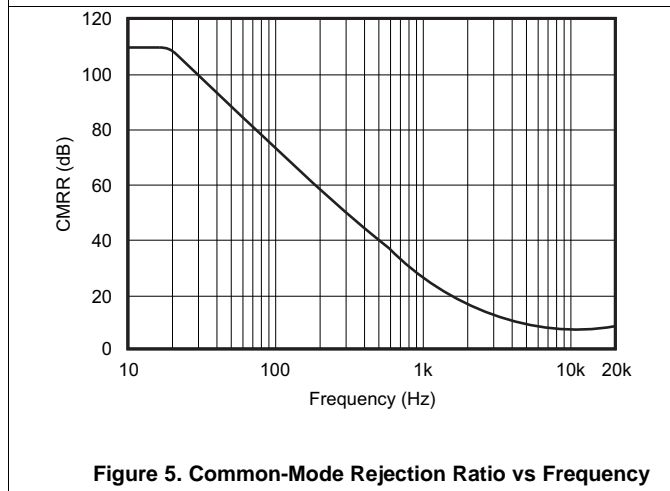
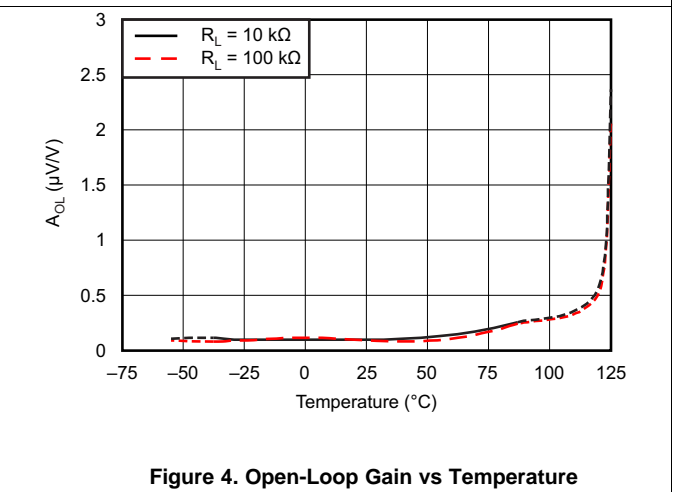
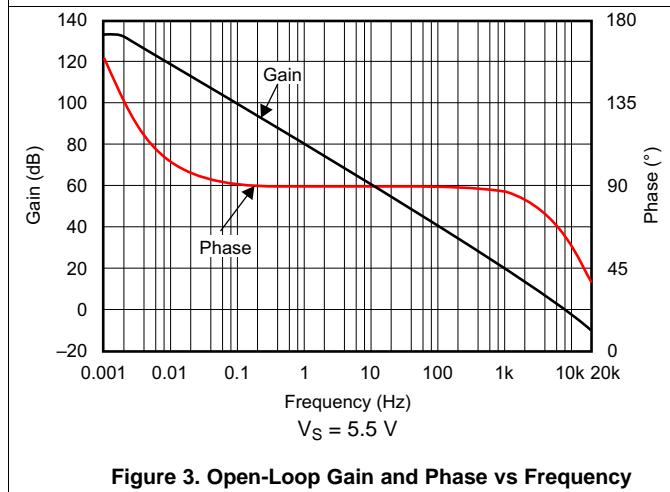
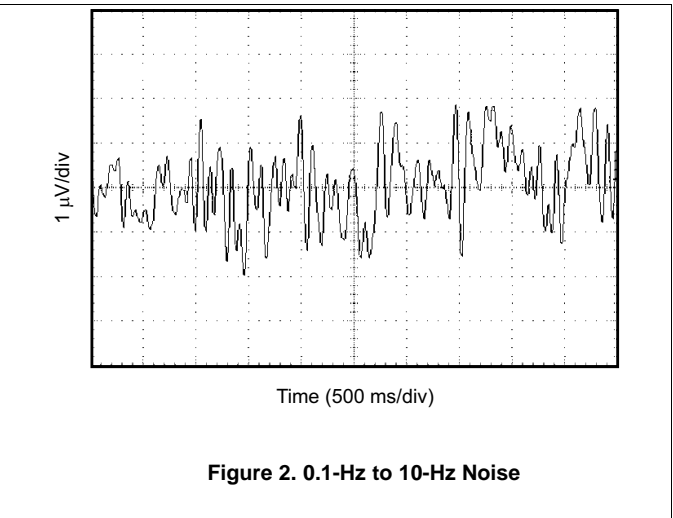
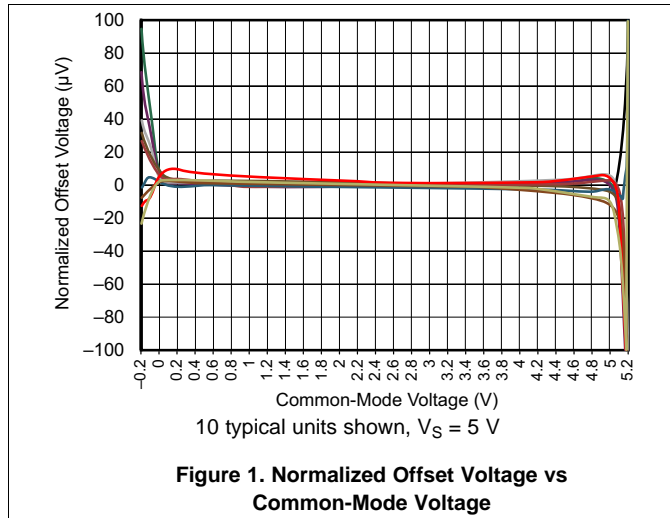
## 6.6 Electrical Characteristics

 $V_S$  (total supply voltage) = 1.8 V to 5.5 V; at  $T_A = 25^\circ\text{C}$ , and  $R_L = 100\text{ k}\Omega$  connected to  $V_S / 2$  (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFFSET VOLTAGE</b>						
$V_{OS}$	Input offset voltage	At $T_A = 25^\circ\text{C}$		0.4	2	mV
		At $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		0.85		
$dV_{OS}/dT$	Drift	At $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		0.5		$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$V_S = 1.8\text{ V}$ to $5.5\text{ V}$	80	94		dB
<b>INPUT VOLTAGE RANGE</b>						
$V_{CM}$	Common-mode voltage range		$V_-$		$V_+$	V
CMRR	Common-mode rejection ratio	$(V_-) \leq V_{CM} \leq (V_+)$	80	110		dB
<b>INPUT BIAS CURRENT</b>						
$I_B$	Input bias current	At $T_A = 25^\circ\text{C}$		10		pA
		At $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$		See Figure 8		
$I_{OS}$	Input offset current			10		pA
<b>INPUT IMPEDANCE</b>						
$Z_{ID}$	Differential			$10^{13} \parallel 3$		$\Omega \parallel \text{pF}$
$Z_{IC}$	Common-mode			$10^{13} \parallel 6$		$\Omega \parallel \text{pF}$
<b>NOISE</b>						
$E_n$	Input voltage noise	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		4		$\mu\text{V}_{PP}$
$e_n$	Input voltage noise density	$f = 1\text{ kHz}$		300		$\text{nV}/\sqrt{\text{Hz}}$
$i_n$	Input current noise density	$f = 1\text{ kHz}$		1		$\text{fA}/\sqrt{\text{Hz}}$
<b>OPEN-LOOP GAIN</b>						
$A_{OL}$	Open-loop voltage gain	At $V_S = 5.5\text{ V}$ , $100\text{ mV} \leq V_O \leq (V_+) - 100\text{ mV}$ , $R_L = 100\text{ k}\Omega$		130		dB
		At $V_S = 5.5\text{ V}$ , $500\text{ mV} \leq V_O \leq (V_+) - 500\text{ mV}$ , $R_L = 10\text{ k}\Omega$	80	120		
<b>OUTPUT</b>						
$V_O$	Voltage output swing from rail	$R_L = 10\text{ k}\Omega$			25	mV
$I_{SC}$	Short-circuit current			10		mA
$C_{LOAD}$	Capacitive load drive			See Figure 10		
<b>FREQUENCY RESPONSE</b>						
GBP	Gain bandwidth product			12		kHz
SR	Slew rate	$G = 1$		0.005		$\text{V}/\mu\text{s}$
$t_{OR}$	Overload recovery time	$V_{IN} \times \text{gain} = V_S$		250		$\mu\text{s}$
<b>POWER SUPPLY</b>						
$V_S$	Specified voltage range		1.8		5.5	V
$I_Q$	Quiescent current	$I_O = 0\text{ mA}$ , at $V_S = 5.5\text{ V}$		800	1300	nA
<b>TEMPERATURE</b>						
	Specified range		-40		85	$^\circ\text{C}$
$T_A$	Operating range		-40		125	$^\circ\text{C}$

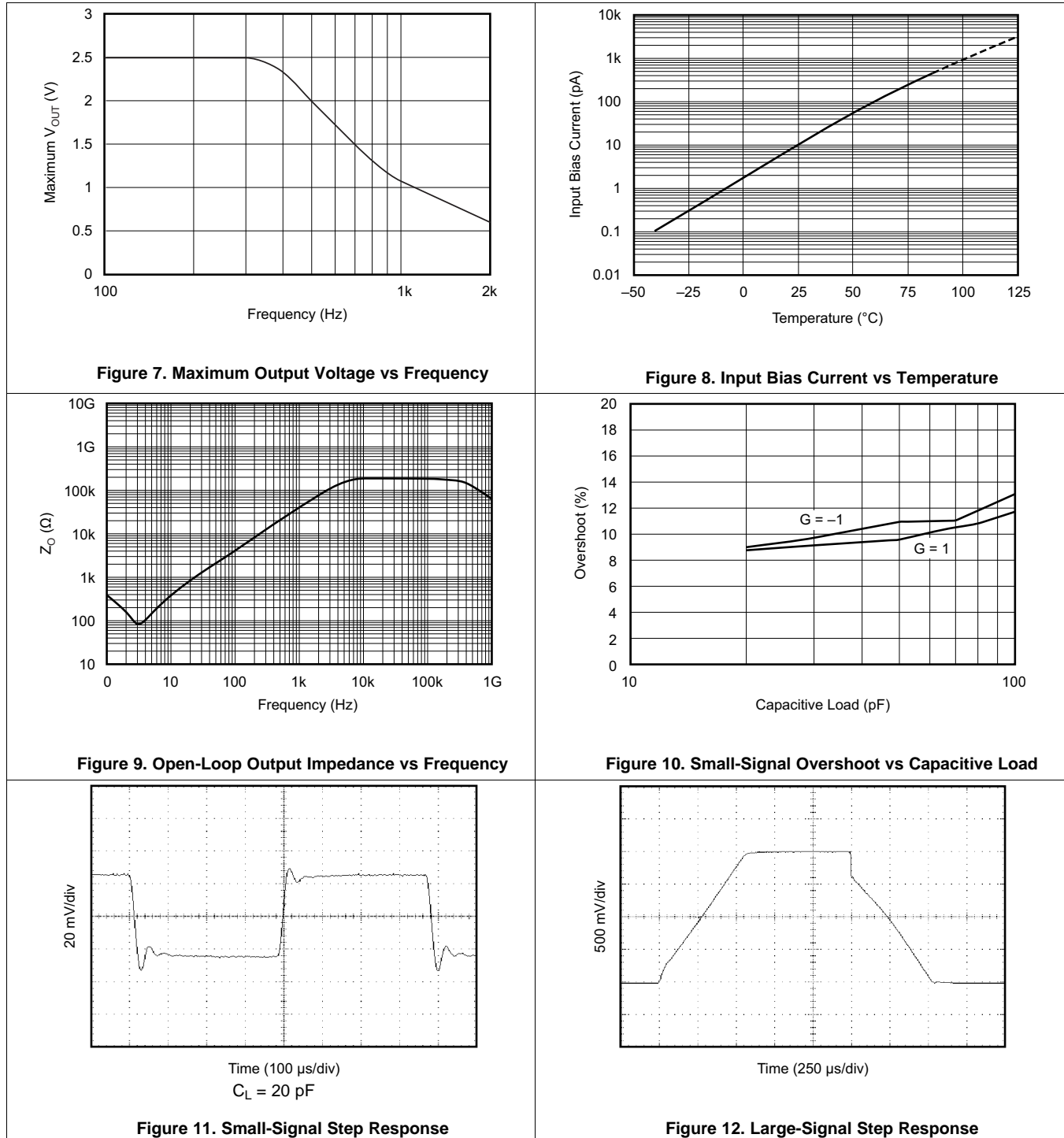
## 6.7 Typical Characteristics

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ , and  $R_L = 100\text{ k}\Omega$  connected to  $V_S / 2$  (unless otherwise noted)



### Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ , and  $R_L = 100\text{ k}\Omega$  connected to  $V_S / 2$  (unless otherwise noted)





### Typical Characteristics (continued)

at  $T_A = 25^\circ\text{C}$ ,  $V_S = 5\text{ V}$ , and  $R_L = 100\text{ k}\Omega$  connected to  $V_S / 2$  (unless otherwise noted)

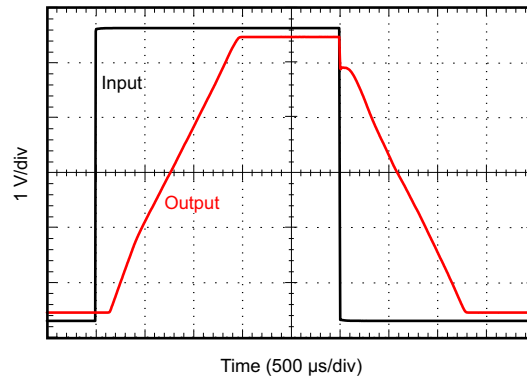


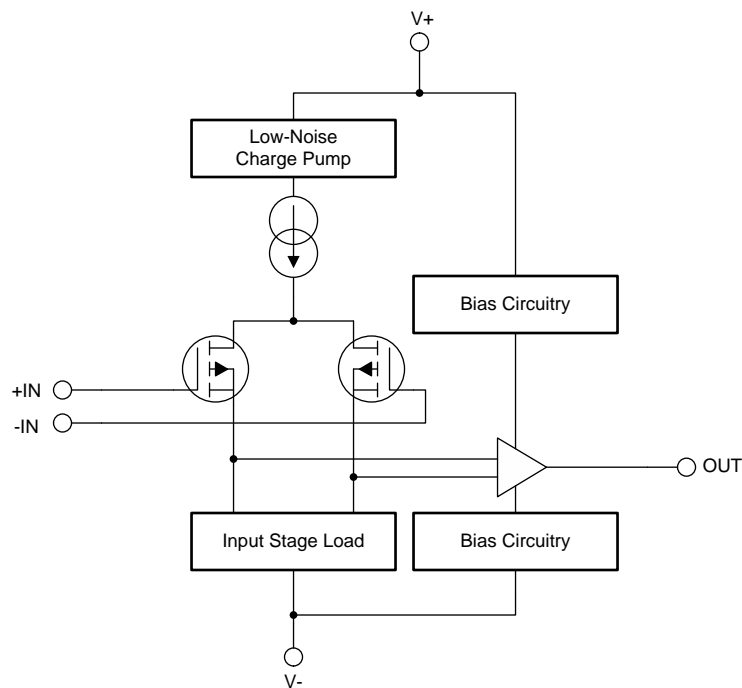
Figure 13. Overload Recovery

## 7 Detailed Description

### 7.1 Overview

The TLVx369 family of operational amplifiers minimizes power consumption and operates on supply voltages as low as 1.8 V. The zero-crossover distortion circuitry enables high linearity over the full input common-mode range, achieving true rail-to-rail input from a 1.8-V to 5.5-V single supply.

### 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Operating Voltage

The TLV369 series op amps are fully specified and tested from 1.8 V to 5.5 V ( $\pm 0.9$  V to  $\pm 2.75$  V). Parameters that vary significantly with supply voltage are described in the [Typical Characteristics](#) section.

### 7.3.2 Input Common-Mode Voltage Range

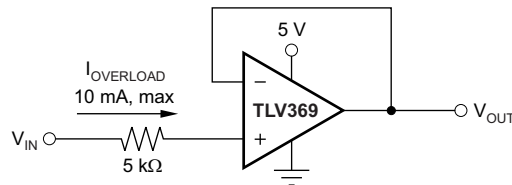
The TLV369 family is designed to eliminate the input offset transition region typically present in most rail-to-rail, complementary-stage operational amplifiers, allowing the TLV369 family of amplifiers to provide superior common-mode performance over the entire input range.

The input common-mode voltage range of the TLV369 family typically extends to each supply rail. CMRR is specified from the negative rail to the positive rail; see [Figure 1](#), *Normalized Offset Voltage vs Common-Mode Voltage*.

### 7.3.3 Protecting Inputs from Overvoltage

Input currents are typically 10 pA. However, large inputs (greater than 500 mV beyond the supply rails) can cause excessive current to flow in or out of the input pins. Therefore, in addition to keeping the input voltage between the supply rails, the input current must also be limited to less than 10 mA. This limiting is easily accomplished with an input resistor, as shown in [Figure 14](#).

A current-limiting resistor is required if the input voltage exceeds the supply rails by  $\geq 0.5$  V.



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**Figure 14. Input Current Protection for Voltages That Exceed the Supply Voltage**

## 7.4 Device Functional Modes

The TLV369 family has a single functional mode. These devices are powered on as long as the power-supply voltage is between 1.8 V ( $\pm 0.9$  V) and 5.5 V ( $\pm 2.75$  V).

## 8 Application and Implementation

### NOTE

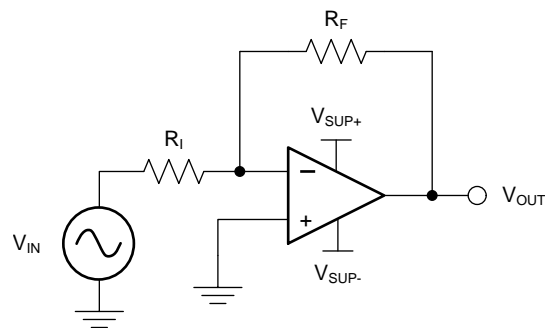
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

When designing for ultra-low power, choose system components carefully. To minimize current consumption, select large-value resistors. Any resistors can react with stray capacitance in the circuit and the input capacitance of the operational amplifier. These parasitic RC combinations can affect the stability of the overall system. Use of a feedback capacitor assures stability and limits overshoot or gain peaking.

### 8.2 Typical Application

A typical application for an operational amplifier is an inverting amplifier, as shown in [Figure 15](#). An inverting amplifier takes a positive voltage on the input and outputs a signal inverted to the input, making a negative voltage of the same magnitude. In the same manner, the amplifier also makes negative input voltages positive on the output. In addition, amplification can be added by selecting the input resistor  $R_I$  and the feedback resistor  $R_F$ .



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**Figure 15. Application Schematic**

#### 8.2.1 Design Requirements

The supply voltage must be chosen to be larger than the input voltage range and the desired output range. The limits of the input common-mode range ( $V_{CM}$ ) and the output voltage swing to the rails ( $V_O$ ) must also be considered. For instance, this application scales a signal of  $\pm 0.5$  V (1 V) to  $\pm 1.8$  V (3.6 V). Setting the supply at  $\pm 2.5$  V is sufficient to accommodate this application.

## Typical Application (continued)

### 8.2.2 Detailed Design Procedure

Determine the gain required by the inverting amplifier using [Equation 1](#) and [Equation 2](#):

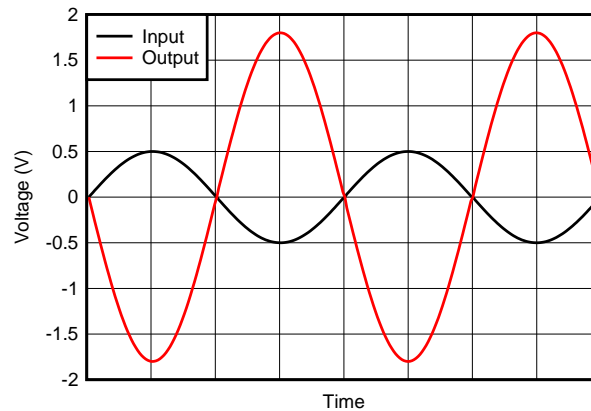
$$A_V = \frac{V_{OUT}}{V_{IN}} \tag{1}$$

$$A_V = \frac{1.8}{-0.5} = -3.6 \tag{2}$$

When the desired gain is determined, choose a value for  $R_I$  or  $R_F$ . Choosing a value in the kilohm range is desirable for general-purpose applications because the amplifier circuit uses currents in the milliamp range. This milliamp current range ensures that the device does not draw too much current. The trade-off is that very large resistors (100s of kilohms) draw the smallest current but generate the highest noise. Very small resistors (100s of ohms) generate low noise but draw high current. This example uses 10 k $\Omega$  for  $R_I$ , meaning 36 k $\Omega$  is used for  $R_F$ . These values are determined by [Equation 3](#):

$$A_V = -\frac{R_F}{R_I} \tag{3}$$

### 8.2.3 Application Curve

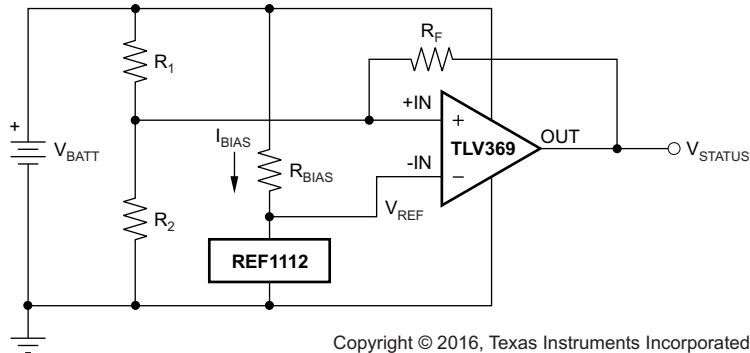


**Figure 16. Inverting Amplifier Input and Output**

## 8.3 System Examples

### 8.3.1 Battery Monitoring

The low operating voltage and quiescent current of the TLV369 series make the family an excellent choice for battery-monitoring applications, as shown in [Figure 17](#).



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**Figure 17. Battery Monitor**

In this circuit,  $V_{STATUS}$  is high as long as the battery voltage remains above 2 V. A low-power reference is used to set the trip point. Resistor values are selected as follows:

1. Selecting  $R_F$ : Select  $R_F$  such that the current through  $R_F$  is approximately 1000 times larger than the maximum bias current over temperature, as given by [Equation 4](#):

$$\begin{aligned} R_F &= \frac{V_{REF}}{1000 (I_{BMAX})} \\ &= \frac{1.2 \text{ V}}{1000 (50 \text{ pA})} \\ &= 24 \text{ M}\Omega \approx 20 \text{ M}\Omega \end{aligned} \tag{4}$$

2. Choose the hysteresis voltage,  $V_{HYST}$ . For battery-monitoring applications, 50 mV is adequate.
3. Calculate  $R_1$  as calculated by [Equation 5](#):

$$R_1 = R_F \left[ \frac{V_{HYST}}{V_{BATT}} \right] = 20 \text{ M}\Omega \left[ \frac{50 \text{ mV}}{2.4 \text{ V}} \right] = 420 \text{ k}\Omega \tag{5}$$

4. Select a threshold voltage for  $V_{IN}$  rising ( $V_{THRS}$ ) = 2.0 V.
5. Calculate  $R_2$  as given by [Equation 6](#):

$$\begin{aligned} R_2 &= \frac{1}{\left[ \left( \frac{V_{THRS}}{V_{BATT}} \right) - \frac{1}{R_1} - \frac{1}{R_1} \right]} \\ &= \frac{1}{\left[ \left( \frac{2 \text{ V}}{1.2 \text{ V} \times 420 \text{ k}\Omega} \right) - \frac{1}{420 \text{ k}\Omega} - \frac{1}{20 \text{ M}\Omega} \right]} \\ &= 650 \text{ k}\Omega \end{aligned} \tag{6}$$

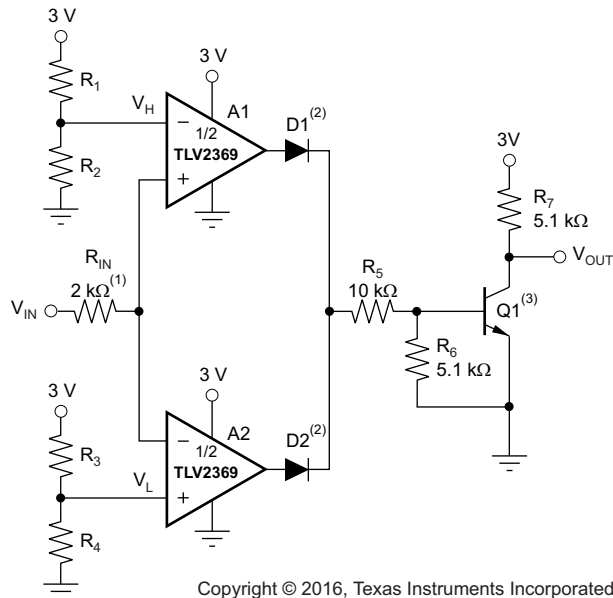
6. Calculate  $R_{BIAS}$ : The minimum supply voltage for this circuit is 1.8 V. The REF1112 has a current requirement of 1.2  $\mu$ A (max). Providing the REF1112 with 2  $\mu$ A of supply current assures proper operation. Therefore,  $R_{BIAS}$  is as given by [Equation 7](#).

$$R_{BIAS} = \frac{V_{BATTMIN}}{I_{BIAS}} = \frac{1.8 \text{ V}}{2 \mu\text{A}} = 0.9 \text{ M}\Omega \tag{7}$$

## System Examples (continued)

### 8.3.2 Window Comparator

Figure 18 shows the TLV2369 used as a window comparator. The threshold limits are set by  $V_H$  and  $V_L$ , with  $V_H$  greater than  $V_L$ . When  $V_{IN}$  is less than  $V_H$ , the output of A1 is low. When  $V_{IN}$  is greater than  $V_L$ , the output of A2 is low. Therefore, both op amp outputs are at 0 V as long as  $V_{IN}$  is between  $V_H$  and  $V_L$ . This architecture results in no current flowing through either diode, Q1 is in cutoff, with the base voltage at 0 V, and  $V_{OUT}$  forced high.



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**Figure 18. TLV2369 as a Window Comparator**

If  $V_{IN}$  falls below  $V_L$ , the output of A2 is high, current flows through D2, and  $V_{OUT}$  is low. Likewise, if  $V_{IN}$  rises above  $V_H$ , the output of A1 is high, current flows through D1, and  $V_{OUT}$  is low. The window comparator threshold voltages are set as shown by Equation 8 and Equation 9:

$$V_H = \frac{R_2}{R_1 + R_2} \quad (8)$$

$$V_L = \frac{R_4}{R_3 + R_4} \quad (9)$$

## 9 Power Supply Recommendations

The TLV369 family is specified for operation from 1.8 V to 5.5 V ( $\pm 0.9$  V to  $\pm 2.75$  V); many specifications apply from  $-40^\circ\text{C}$  to  $+125^\circ\text{C}$ . The *Typical Characteristics* section presents parameters that can exhibit significant variance with regard to operating voltage or temperature.

### CAUTION

Supply voltages larger than 7 V can permanently damage the device (see the *Absolute Maximum Ratings* table).

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement; see the *Layout Guidelines* section.

## 10 Layout

### 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier. Use bypass capacitors to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu\text{F}$  ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from  $V+$  to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current. For more detailed information, see *Circuit Board Layout Techniques*, [SLOA089](#).
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than crossing in parallel with the noisy trace.
- Place the external components as close to the device as possible. Keep  $R_F$  and  $R_G$  close to the inverting input in order to minimize parasitic capacitance, as shown in [Figure 19](#).
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

### 10.2 Layout Example

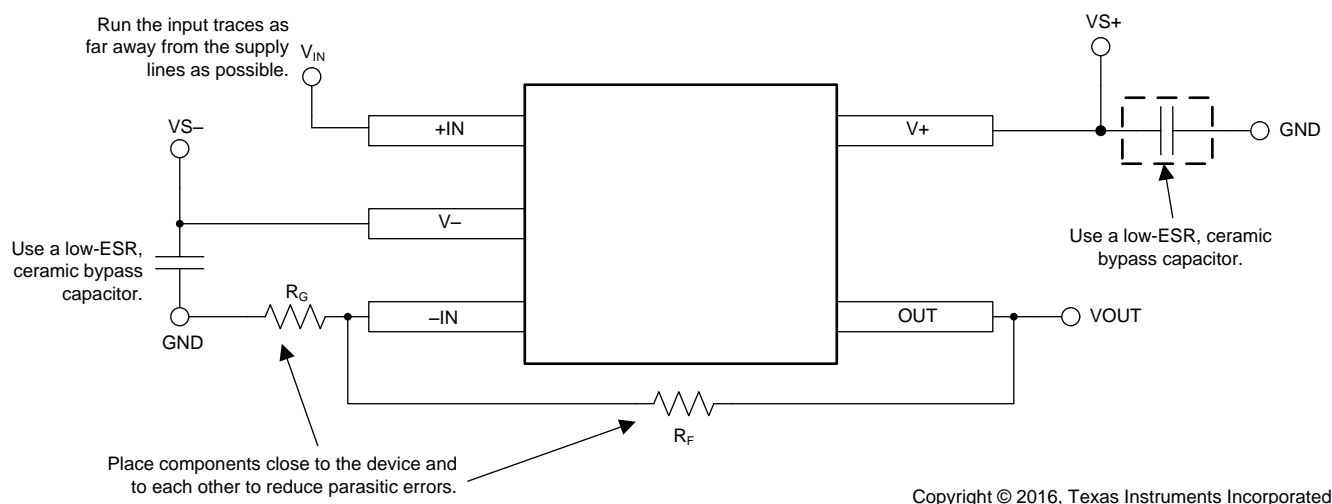
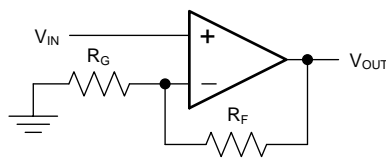


Figure 19. Operational Amplifier Board Layout for Noninverting Configuration



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Figure 20. Schematic Representation of [Figure 19](#)



## 11 器件和文档支持

### 11.1 文档支持

#### 11.1.1 相关文档

使用 TLVx369 时，建议参考下列相关文档，文档下载地址为 [www.ti.com.cn](http://www.ti.com.cn)（除非另外注明）。

- 《REF1112 数据表》，[SBOS283](#)
- 《电路板布局布线技巧》，[SLOA089](#)
- 《运算放大器应用 手册》，[SBOA092](#)
- 《模拟工程师速查参考》，[SLWY038](#)

#### 11.1.1.1 相关链接

表 1 列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，以及样片或购买的快速访问。

表 1. 相关链接

器件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
TLV369	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
TLV2369	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>

### 11.2 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

**TI E2E™ Online Community** *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At [e2e.ti.com](http://e2e.ti.com), you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

### 11.3 商标

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### 11.4 静电放电警告



ESD 可能会损坏该集成电路。德州仪器 (TI) 建议通过适当的预防措施处理所有集成电路。如果不遵守正确的处理措施和安装程序，可能会损坏集成电路。

ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

### 11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2369IDGKR	ACTIVE	VSSOP	DGK	8	2500	RoHS & Green	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV	<a href="#">Samples</a>
TLV2369IDGKT	ACTIVE	VSSOP	DGK	8	250	RoHS & Green	NIPDAU   NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	13JV	<a href="#">Samples</a>
TLV2369IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	TL2369	<a href="#">Samples</a>
TLV369IDCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K	<a href="#">Samples</a>
TLV369IDCKT	ACTIVE	SC70	DCK	5	250	RoHS & Green	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	12K	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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# DGK0008A



# PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



**NOTES:**

PowerPAD is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

# EXAMPLE BOARD LAYOUT

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

# EXAMPLE STENCIL DESIGN

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE  
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.



# EXAMPLE BOARD LAYOUT

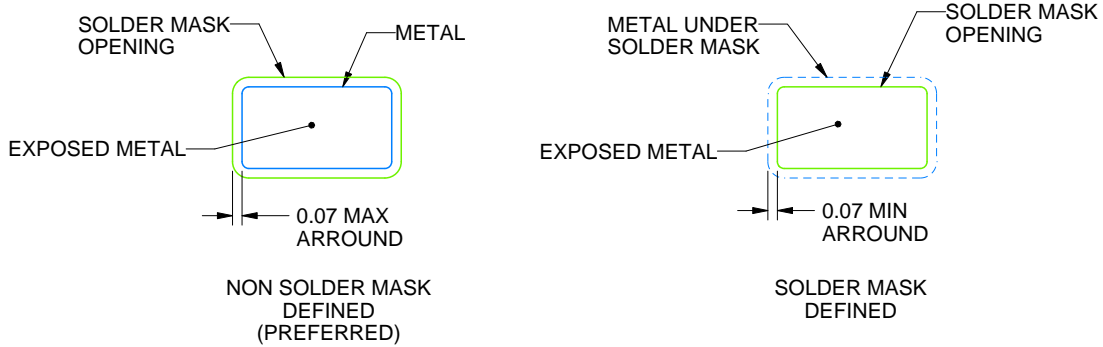
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



# EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 THICK STENCIL  
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.



D0008A

# PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

### NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed  $.006$  [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

# EXAMPLE BOARD LAYOUT

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE  
 EXPOSED METAL SHOWN  
 SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE  
BASED ON .005 INCH [0.125 MM] THICK STENCIL  
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

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